



2015-05

NIPEK8, 19/05/2015

Process 1 wafer to send to grenoble for proximity effect aluminum kids

Wafer batch 0806RR from FZ wafers (525 μ m +/-25 thick)

- **Désoxydation wafer** (Hélène, SPEC)

HF:ODI 1:20, 1'

rinçage ODI 1'

- **evap nouveau canon SPEC (09/03)**

Ti 10 / Al 25 (target Tc = mK)

Pumped over night with valve open -> 7.0e-8mb (ch: 5.0e-8) after filling

DEGAS sources

- Ti 0.5nm/s

P raises > ? on both ch and sas at beginning of crucible heat (@39mA)

-> 3.2e-8 (2.8e-8) gun off

- Al 2nm/s

2.7e-7 @ 420mA (1.9)

-> 6.0e-8 / 5.7e-8 gun off

EVAPORATION

- Ti pump m @ 0.2nm/s -> P_{sas} = 2.4e-8 / P_{ch} = 2.6e-8mb gun off

- Ti 10.4nm @ 0.5nm/s, 0°, spin 16°/s. **P_{evap} = 3.2 / 3.2e-8** -> 2.2/ 2.

- Al 25.47nm (max 35nm on quartz after cool down of source) @ 1nm/s, 0°, P_{evap}

= 1.5 / 1.7e-7 -> 6e-8/ 6e-8 (gun off)

5'50 between end of Ti (shutter close) and beginning of Al (shutter open)

(skept wait time after Ti ramp down)

NB:during Al evap

P_{sas} = 3.1e-8mb @ 235mA

= 5.3e-8mb @ 285mA

= 7.1e-8mb @ 300mA (~0.8nm/s)

= 1.5e-7mb @ 350mA (0.9-1nm/s)